

WHAT IS CLAIMED IS:

1. A method for fabricating a semiconductor device including a concaved capacitor device having a lower electrode, a capacitor dielectric film of a perovskite type high dielectric constant or ferroelectric material formed on said lower electrode and an upper electrode formed on said capacitor dielectric film, comprising a step of:

forming a conducting film to be formed into said lower electrode including sub-steps of:

10 depositing a lower conducting film by sputtering on walls and a bottom of a recess formed in an insulating film on a substrate; and

depositing an upper conducting film on said lower conducting film by CVD.

15 2. The method for fabricating a semiconductor device of Claim 1,

wherein said lower conducting film has a thickness of 0.5 nm through 5 nm.

20 3. A method for fabricating a semiconductor device including a capacitor device having a lower electrode, a capacitor dielectric film of a perovskite type high dielectric constant or ferroelectric material formed on said lower electrode and an upper electrode formed on said capacitor dielectric film, comprising a step of:

25 forming a conducting film to be formed into said upper

electrode including sub-steps of:

depositing a lower conducting film by sputtering;

and

depositing an upper conducting film on said lower

5 conducting film by CVD.

4. The method for fabricating a semiconductor device of
Claim 3,

wherein said capacitor device is a concaved capacitor
device.

10 5. The method for fabricating a semiconductor device of
Claim 3,

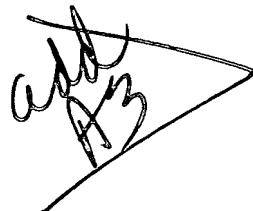
wherein said capacitor device is a stacked capacitor
device.

15 6. The method for fabricating a semiconductor device of
Claim 3,

wherein the CVD is carried out in an oxidizing
atmosphere.

7. The method for fabricating a semiconductor device of
Claim 3,

20 wherein said lower conducting film has a thickness of
0.5 nm through 5 nm.

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